EAST - [09943134 tunnel barrier FG.wsp:1]

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(97) ((float$3 adj gate) same (control adj gate)) same ((((ba
(0) (((float$3 adj gate) same (control adj gate)) same ((((ba
(0) (((float$3 adj gate) same (control adj gate)) same ((((ba
(173565) metal adj oxide
(10) ((((float$3 adj gate) same (control adj gate)) same ((((b
(387) ((float$3 adj gate) same (control adj gate)) and ((((ba
(1) (((float$3 adj gate) same (control adj gate)) and ((((barri
(31) ((float$3 adj gate) same (control adj gate)) and (ald (at
(9) ((((barrier adj height) (energy adj band))) near2 (asymme
(41) ((((float$3 adj gate) same (control adj gate)) same ((((b
(49) (((((barrier adj height) (energy adj band))) near2 (asymr
(49) (((((barrier adj height) (energy adj band))) near2 (asymr
(4453) depletion adj mode
(2) ((((((barrier adj height) (energy adj band))) near2 (asymm
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(((((barrier adj height) (energy adj band))) near2 (asymmetr$4 differen$2)) and (float$3 adj gate) and (control adj gate)) ((((((float$3 adj gate) same (control adj gate)) same ((((barrier near (height tunnel)) ((energy diagram) near band))
) (work adj function))) and (metal adj oxide)) (((float$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit$3))))

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1	☐	☑	Faraone, Lorenzo	US 4757360 A	19880712	6	Floating gate memory device with facing asperities on floating and control gates	257/317	257/900; 257/E29.304	
2	☐	☑	Lee, Jongho et al.	US 20020106536 A1	20020808	13	Dielectric layer for semiconductor device and method of manufacturing the same	428/702	428/428	
3	☐	☑	Lee, Woo-Hyeong et al.	US 5923056 A	19990713	6	Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxi	257/192	257/410; 257/411;	
4	☐	☑	Muralidhar, Ramachandran et al.	US 6320784 B1	20011120	7	Memory cell and method for programming thereof	365/151	257/E29.301; 257/E29.308;	
5	☐	☑	Nguyen, Bich-Yen et al.	US 20020137250 A1	20020926	10	High K dielectric film and method for making	438/53		
6	☐	☑	Uchida, Hidetsugu	US 6229175 B1	20010508	24	Nonvolatile memory	257/315	257/298; 257/316;	
7	☐	☐	Ahn, Kie Y. et al.	US 20020130338 A1	20020919	9	Structures, methods, and systems for ferroelectric memory transistors	257/295		
8	☐	☐	Ahn, Kie Y. et al.	US 20020086556 A1	20020704	11	Methods of forming silicon-doped aluminum oxide, and methods of forming transistors and memory devices	438/785		

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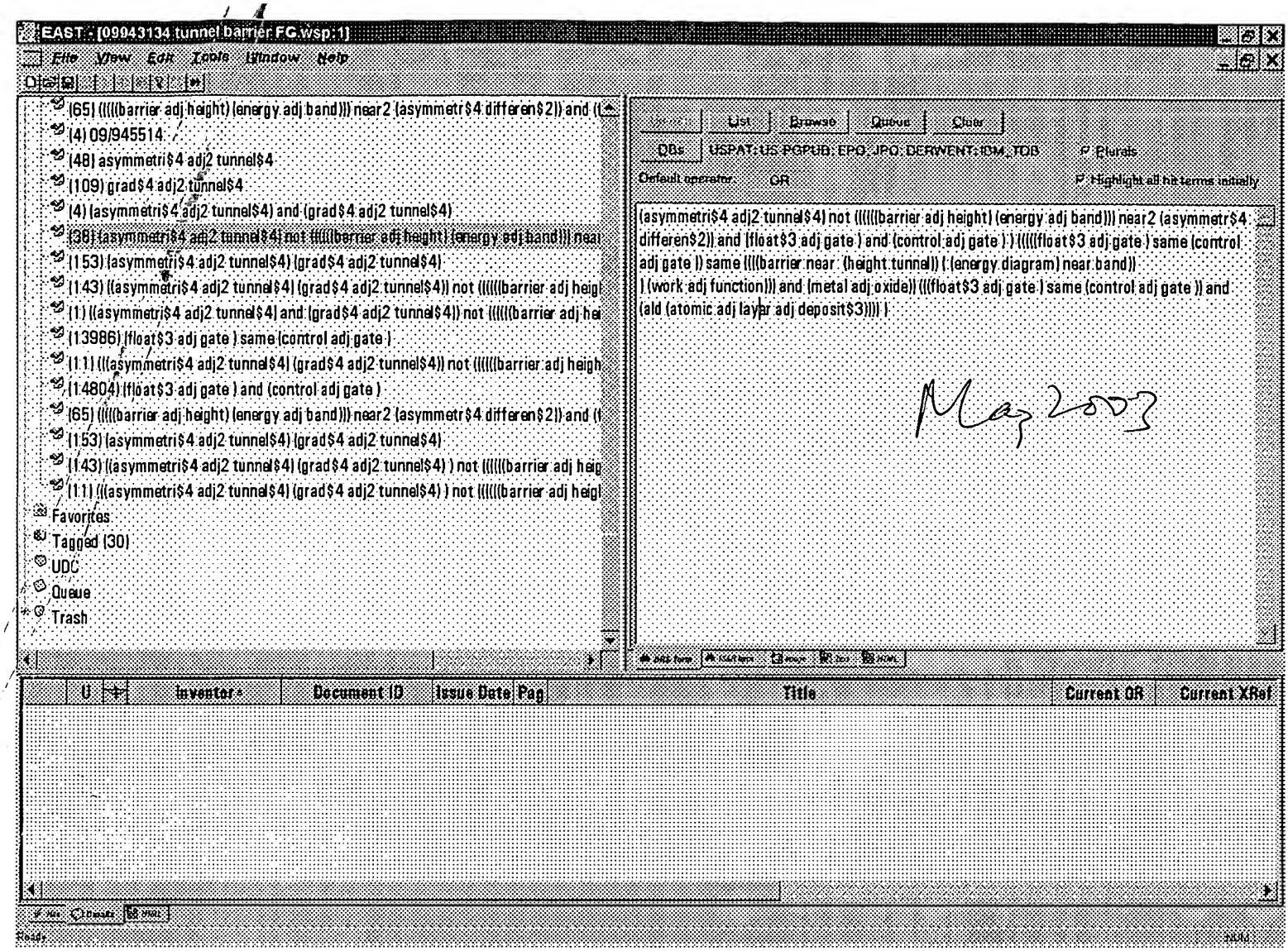
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(65) (((((barrier adj height) (energy adj band))) near2 (asymmetri$4 differen$2)) and ((
(4) 09/945514
(48) asymmetri$4 adj2 tunnel$4
(109) grad$4 adj2 tunnel$4
(4) (asymmetri$4 adj2 tunnel$4) and (grad$4 adj2 tunnel$4)
(36) (asymmetri$4 adj2 tunnel$4) not ((((((barrier adj height) (energy adj band))) near
(153) (asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)
(143) ((asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)) not ((((((barrier adj heig
(1) ((asymmetri$4 adj2 tunnel$4) and (grad$4 adj2 tunnel$4)) not ((((((barrier adj hei
(13986) (float$3 adj gate) same (control adj gate)
(11) (((asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)) not ((((((barrier adj heigh
(14804) (float$3 adj gate) and (control adj gate)
(65) (((((barrier adj height) (energy adj band))) near2 (asymmetr$4 differen$2)) and ((
(153) (asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)
(143) ((asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)) not ((((((barrier adj heig
(11) (((asymmetri$4 adj2 tunnel$4) (grad$4 adj2 tunnel$4)) not ((((((barrier adj heigl
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(asymmetri$4 adj2 tunnel$4) not ((((((barrier adj height) (energy adj band))) near2 (asymmetr$4 differen$2)) and (float$3 adj gate) and (control adj gate)) ((((((float$3 adj gate) same (control adj gate)) same ((((barrier near (height tunnel)) ((energy diagram) near band))
) (work adj function))) and (metal adj oxide)) (((float$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit$3)))))
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- Active
  - L7: (4) ("6210999" "6541280").pn.
- Failed
- Saved
  - (1) 09/948877
  - (1813) tunnel adj barrier
  - (5) low adj (tunnel adj barrier)
  - (109488) asymmetri$4
  - (0) asymmetri$4 adj (low adj (tunnel adj barrier))
  - (12792) (float$3 adj gate) same (control adj gate)

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	D		Inventor	Document ID	Issue Date	Page	Title	Current OR	Current XRef
1	☐	☑	Gardner, Mark I. et al.	US 6210999 B1	20010403	14	Method and test structure for low-temperature integration of high dielectric constant gate dielectrics into self-aligned semiconductor devices	438/183	257/332; 257/E21.209;
2	☐	☑	Kaushik, Vidya S. et al.	US 6541280 B2	20030401	8	High K dielectric film	438/3	257/E29.162; 361/311;
3	☑	☐	GARDNER, M I et al.	US 6210999 B	20010403		Semiconductor device for fabricating MOS IC, comprises gate dielectric having high dielectric constant and gate conductor laid one above another sequentially in trench formed a		
4	☑	☐	KAUSHIK, V S et al.	US 20020137317 A	20030401	8	Semiconductor structure for semiconductor devices, has gate dielectric layer containing lanthanum, aluminum and oxygen, and electrode layer, formed on semiconductor substrate		

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